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## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



### Product Summary

<b>BV<sub>DSS</sub></b>	<b>R<sub>DS(ON)</sub> max</b>	<b>I<sub>D</sub> T<sub>C</sub> = +25°C</b>
40V	10mΩ @ V <sub>GS</sub> = 10V	100A

### Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

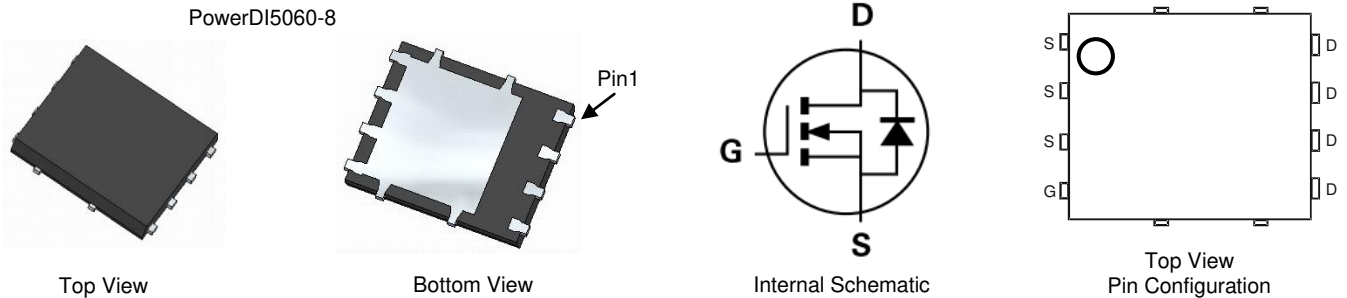
- Engine Management Systems
- DC-DC Converters
- Body Control Electronics

### Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Q<sub>g</sub> – Minimizes Switching Loss
- Low R<sub>DS(ON)</sub> – Minimizes On State Loss
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

### Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

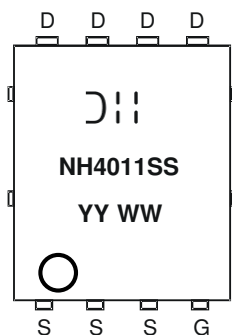


### Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH4011SPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to [http://www.diodes.com/product\\_compliance\\_definitions.html](http://www.diodes.com/product_compliance_definitions.html).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

### Marking Information



☺;|| = Manufacturer’s Marking  
 NH4011SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 16 = 2016)  
 WW = Week (01 to 53)



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	12.9	A
		10.8	A
	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C (Note 8)	100	A
		65	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	2.7	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I <sub>DM</sub>	90	A
Avalanche Current, L = 1mH	I <sub>AS</sub>	18.7	A
Avalanche Energy, L = 1mH	E <sub>AS</sub>	176	mJ

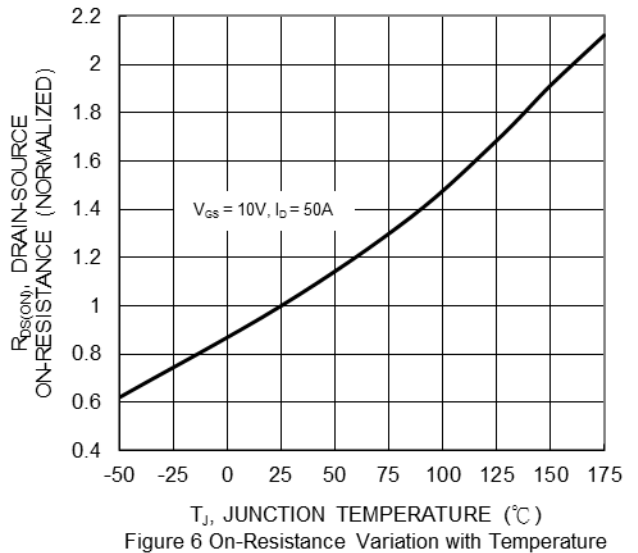
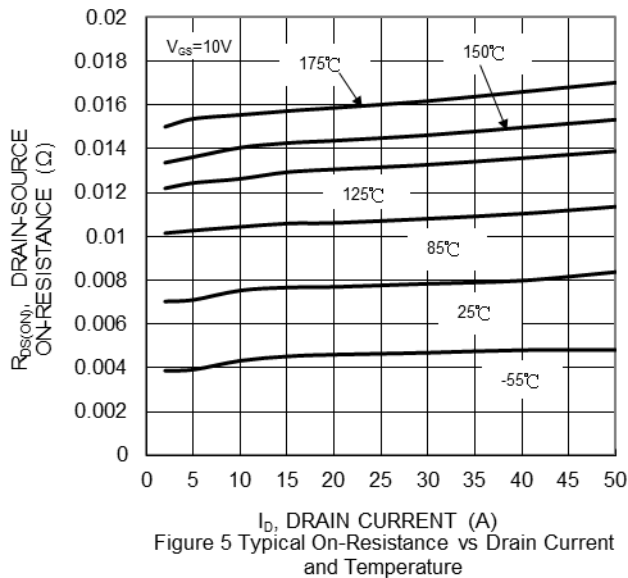
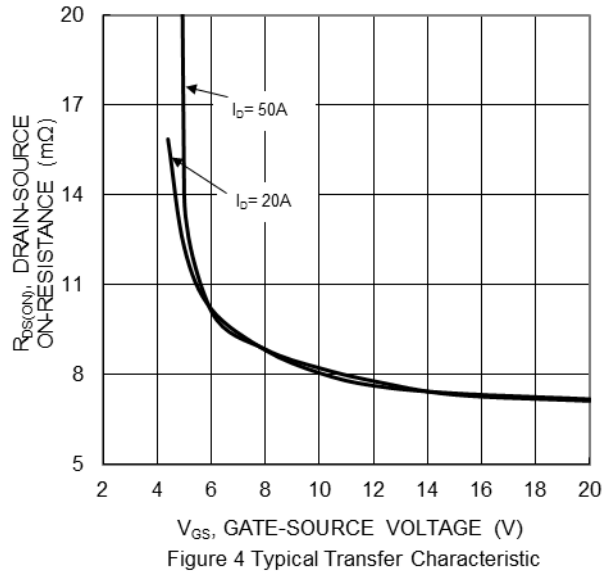
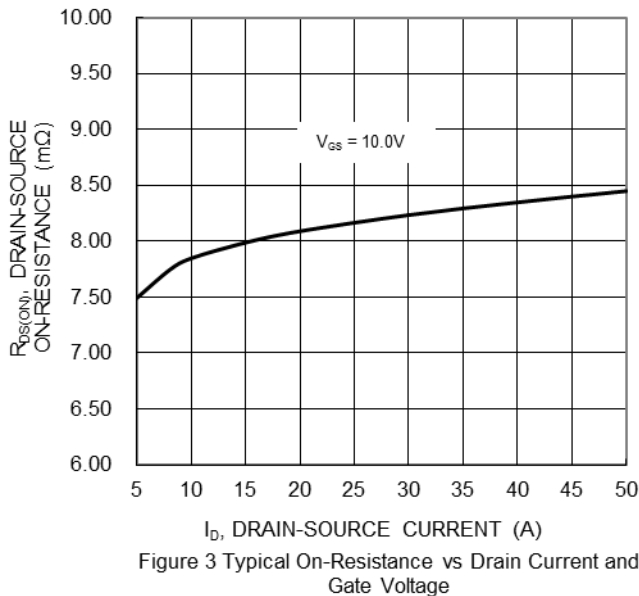
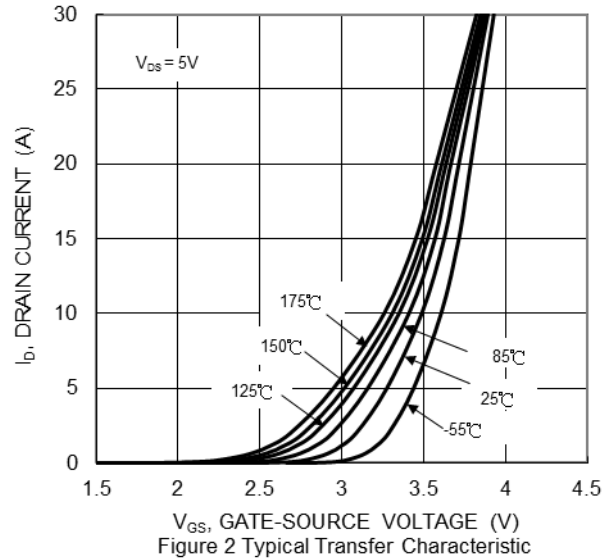
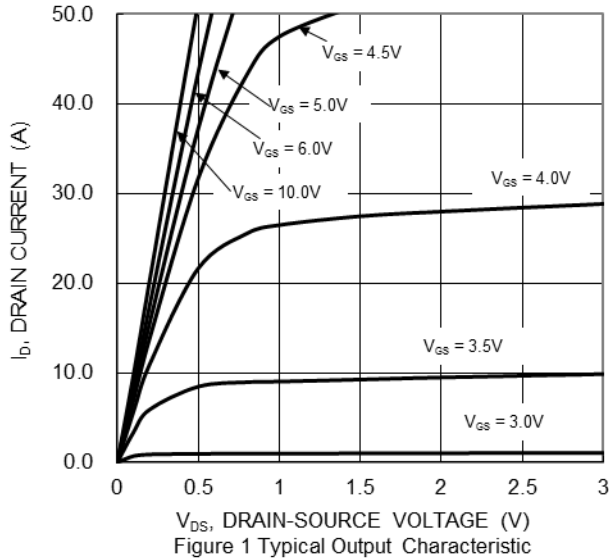
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	60	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	150	W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	1	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	8.5	10	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 50A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	1405	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	247	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	108	—		
Gate Resistance	R <sub>g</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	25.5	—	nC	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A
Gate-Source Charge	Q <sub>gs</sub>	—	4.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	6.9	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.6	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 50A, R <sub>G</sub> = 3.5Ω
Turn-On Rise Time	t <sub>R</sub>	—	3.7	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	16	—		
Turn-Off Fall Time	t <sub>F</sub>	—	5.1	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	22.1	—	ns	I <sub>F</sub> = 50A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	13.4	—	nC	

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.



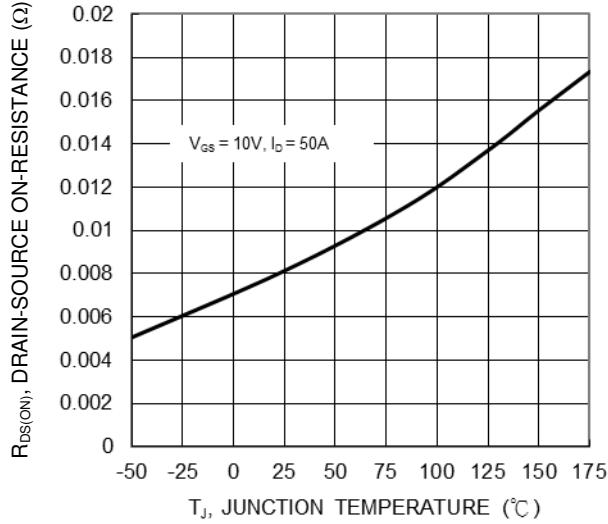


Figure 7 On-Resistance Variation with Temperature

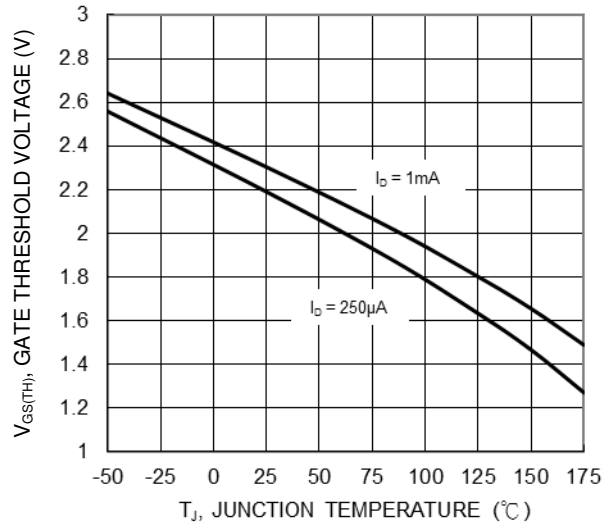


Figure 8 Gate Threshold Variation vs Temperature

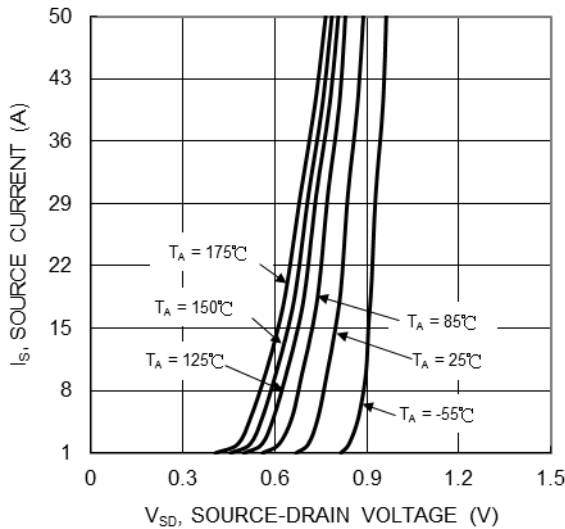


Figure 9 Diode Forward Voltage vs Current

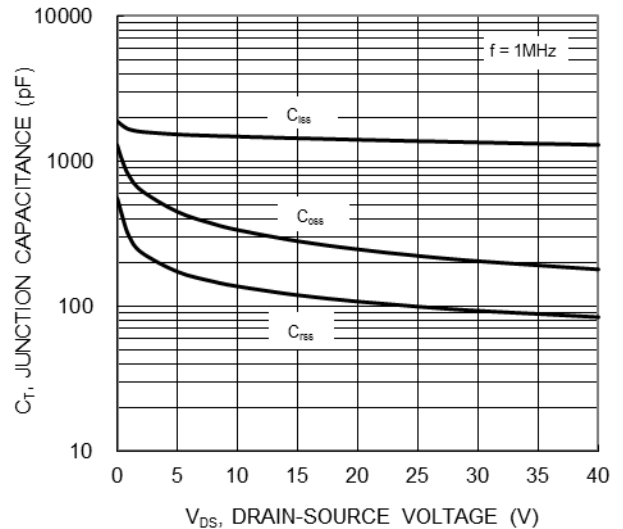


Figure 10 Typical Junction Capacitance

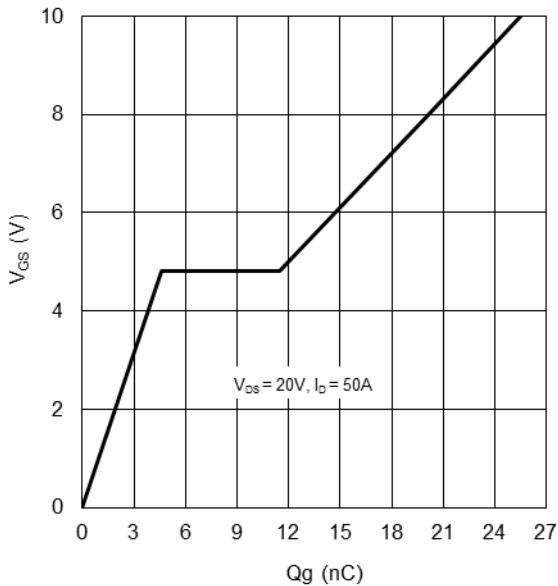


Figure 11 Gate Charge

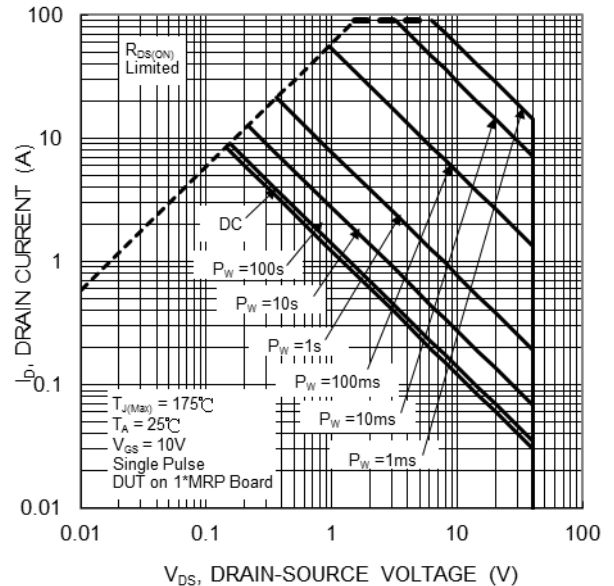
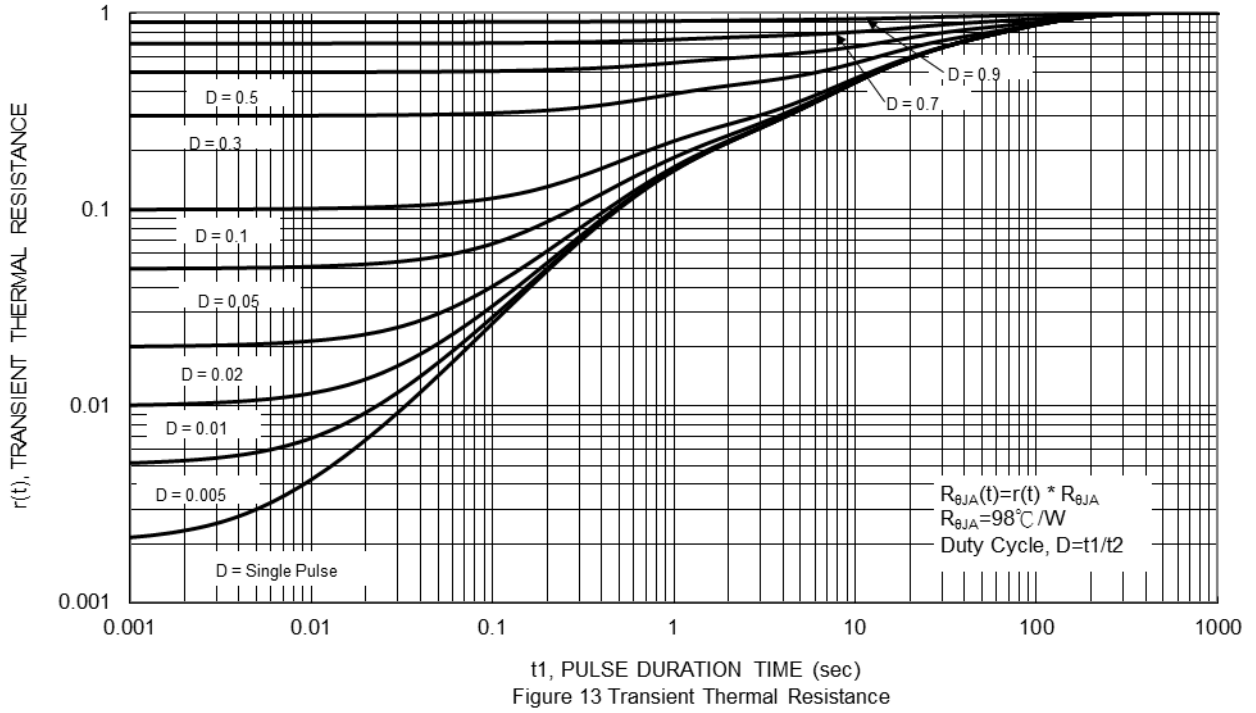


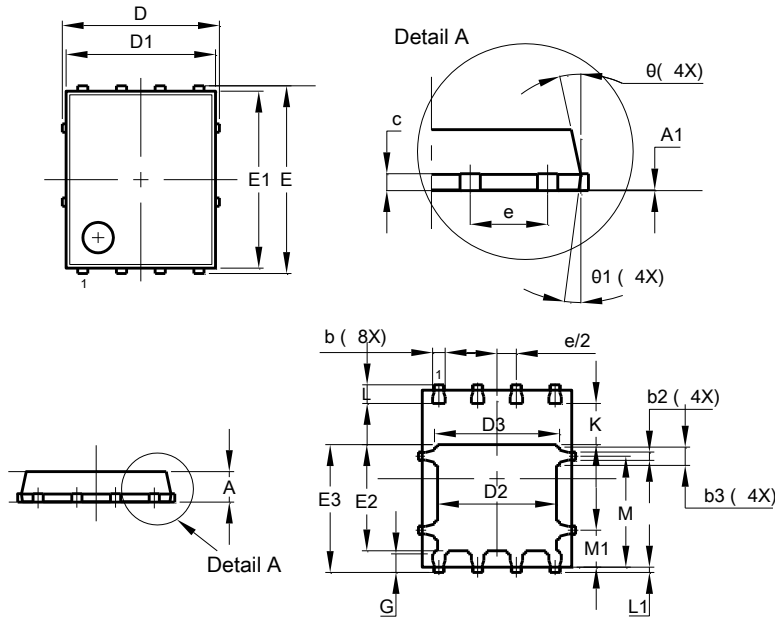
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**

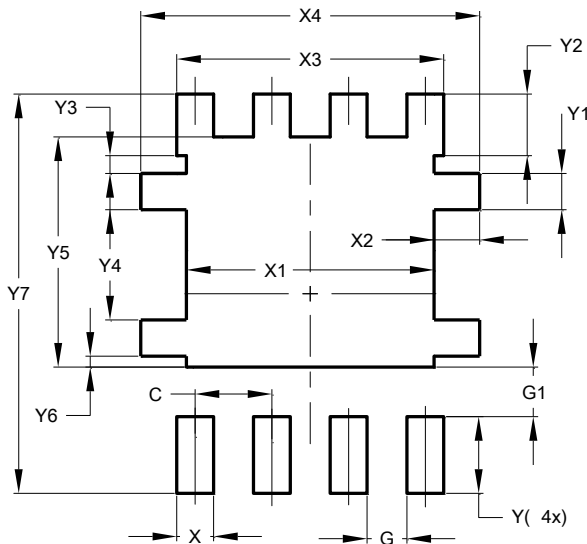


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
$\theta$	10°	12°	11°
$\theta$ 1	6°	8°	7°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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